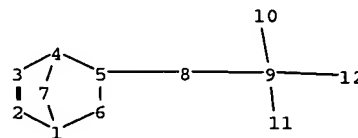
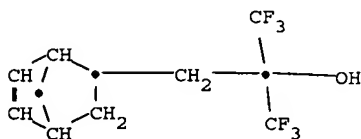
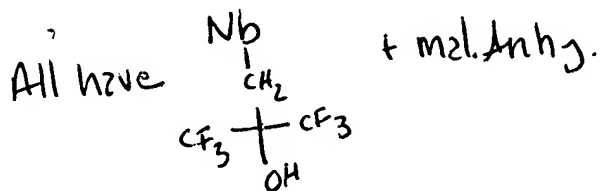


SEARCH: CA REG. File
 Structure search. Polymers
 in claim 4.



10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

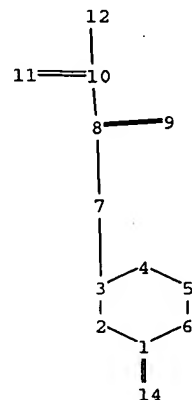
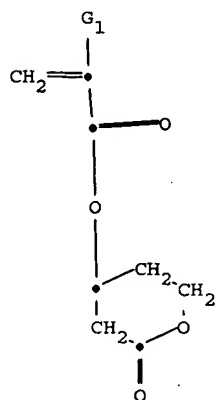

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN




10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN


10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

10/719,905, 8/16/05
 maleic anhydride in (P)
 108-31-6/CRN

[illegible]

□)(■% ⑧□■◆ 

L30 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2005:98956 CAPLUS

DN 142:207614

TI Photoresist polymer and photoresist composition containing the same

IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun

PA S. Korea

SO U.S. Pat. Appl. Publ., 17 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI	KR 2003-52337	A	20030729		

AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I (X1-4 = CH2, CH2CH2, S; R1,2 = H, CH3, CF3; R3 = C1-20 alkyl, etc.; R4 = C1-20 hydroxyalkyl, etc.; R5 = H, C1-20 hydroxyalkyl, etc.; m = 0-2; and n = 0, 1). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT 836623-60-0P 836623-61-1P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(photoresist polymer for photoresist composition)

RN 836623-60-0 CAPLUS

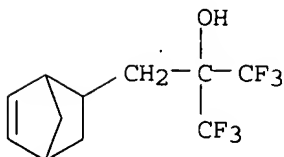
CN 2-Propenoic acid, 2-methyl-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 196314-61-1

CMF C11 H12 F6 O

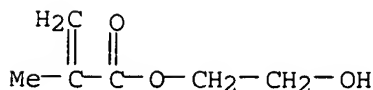
Mj Appl.



CM 2

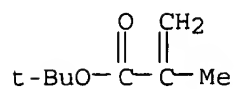
CRN 868-77-9

CMF C6 H10 O3



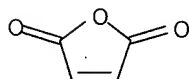
CM 3

CRN 585-07-9
CMF C8 H14 O2



CM 4

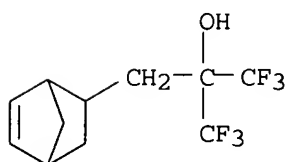
CRN 108-31-6
CMF C4 H2 O3



RN 836623-61-1 CAPLUS
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione and 2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

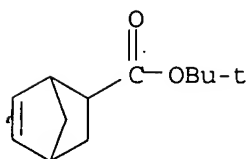
CM 1

CRN 196314-61-1
CMF C11 H12 F6 O



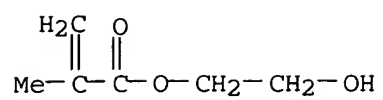
CM 2

CRN 154970-45-3
CMF C12 H18 O2



CM 3

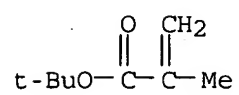
CRN 868-77-9
CMF C6 H10 O3



CM 4

CRN 585-07-9

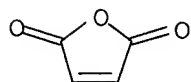
CMF C8 H14 O2



CM 5

CRN 108-31-6

CMF C4 H2 O3



=>

L32 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2005:98956 CAPLUS
 DN 142:207614
 TI Photoresist polymer and photoresist composition containing the same
 IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae
 Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun
 PA S. Korea
 SO U.S. Pat. Appl. Publ., 17 pp.
 CODEN: USXXCO
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI	KR 2003-52337	A	20030729		

AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I (X1-4 = CH2, CH2CH2, S; R1,2 = H, CH3, CF3; R3 = C1-20 alkyl, etc.; R4 = C1-20 hydroxyalkyl, etc.; R5 = H, C1-20 hydroxyalkyl, etc.; m = 0-2; and n = 0, 1). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT **836623-58-6P 836623-59-7P**
 RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (photoresist polymer for photoresist composition)

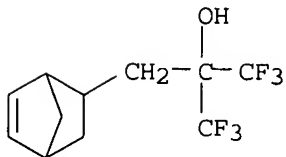
RN 836623-58-6 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with
 α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol,
 2,5-furandione and 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl
 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 196314-61-1

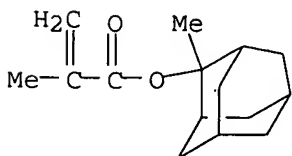
CMF C11 H12 F6 O



CM 2

CRN 177080-67-0

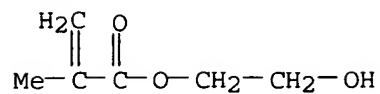
CMF C15 H22 O2



CM 3

CRN 868-77-9

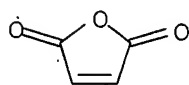
CMF C6 H10 O3



CM 4

CRN 108-31-6

CMF C4 H2 O3



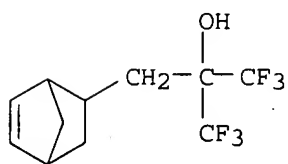
RN 836623-59-7 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with bicyclo[2.2.1]hept-2-ene, α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 196314-61-1

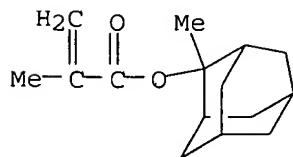
CMF C11 H12 F6 O



CM 2

CRN 177080-67-0

CMF C15 H22 O2



CM 3

CRN 868-77-9

L12 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2005:98956 CAPLUS
 DN 142:207614
 TI Photoresist polymer and photoresist composition containing the same
 IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae
 Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun
 PA S. Korea
 SO U.S. Pat. Appl. Publ., 17 pp.
 CODEN: USXXCO
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI	KR 2003-52337	A	20030729		

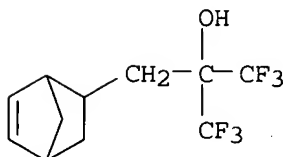
AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I (X1-4 = CH₂, CH₂CH₂, S; R1,2 = H, CH₃, CF₃; R3 = C1-20 alkyl, etc.; R4 = C1-20 hydroxyalkyl, etc.; R5 = H, C1-20 hydroxyalkyl, etc.; m = 0-2; and n = 0, 1). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT **836623-58-6P 836623-59-7P**
 RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (photoresist polymer for photoresist composition)

RN 836623-58-6 CAPLUS
 CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with
 α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol,
 2,5-furandione and 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl
 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

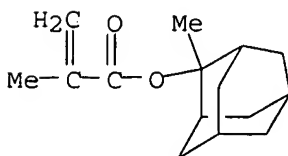
CM 1

CRN 196314-61-1
 CMF C11 H12 F6 O



CM 2

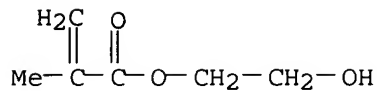
CRN 177080-67-0
 CMF C15 H22 O2



CM 3

CRN 868-77-9

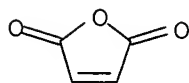
CMF C6 H10 O3



CM 4

CRN 108-31-6

CMF C4 H2 O3



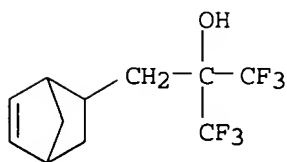
RN 836623-59-7 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with bicyclo[2.2.1]hept-2-ene, α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 196314-61-1

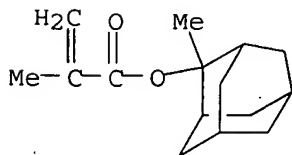
CMF C11 H12 F6 O



CM 2

CRN 177080-67-0

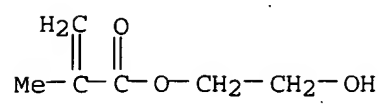
CMF C15 H22 O2



CM 3

CRN 868-77-9

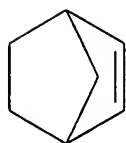
CMF C6 H10 O3



CM 4

CRN 498-66-8

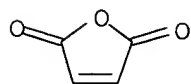
CMF C7 H10



CM 5

CRN 108-31-6

CMF C4 H2 O3



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L16 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2005:98956 CAPLUS
 DN 142:207614
 TI Photoresist polymer and photoresist composition containing the same
 IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae
 Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun
 PA S. Korea
 SO U.S. Pat. Appl. Publ., 17 pp.
 CODEN: USXXCO
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI	KR 2003-52337	A	20030729		

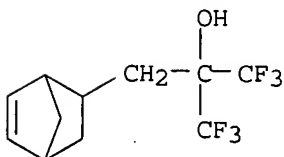
AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I (X1-4 = CH2, CH2CH2, S; R1,2 = H, CH3, CF3; R3 = Cl-20 alkyl, etc.; R4 = Cl-20 hydroxyalkyl, etc.; R5 = H, Cl-20 hydroxyalkyl, etc.; m = 0-2; and n = 0, 1). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT **836623-60-0P 836623-61-1P**
 RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (photoresist polymer for photoresist composition)

RN 836623-60-0 CAPLUS
 CN 2-Propenoic acid, 2-methyl-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

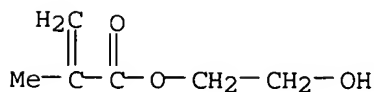
CM 1

CRN 196314-61-1
 CMF C11 H12 F6 O



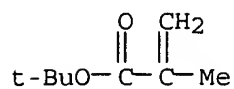
CM 2

CRN 868-77-9
 CMF C6 H10 O3



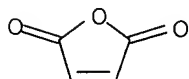
CM 3

CRN 585-07-9
CMF C8 H14 O2



CM 4

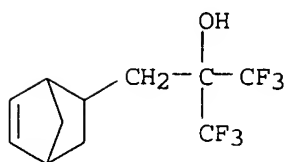
CRN 108-31-6
CMF C4 H2 O3



RN 836623-61-1 CAPLUS
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester,
polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-
2-ethanol, 1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione and
2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

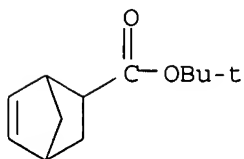
CM 1

CRN 196314-61-1
CMF C11 H12 F6 O



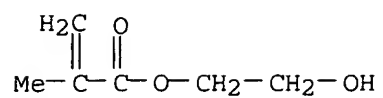
CM 2

CRN 154970-45-3
CMF C12 H18 O2



CM 3

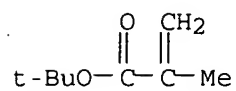
CRN 868-77-9
CMF C6 H10 O3



CM 4

CRN 585-07-9

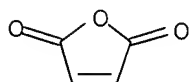
CMF C8 H14 O2



CM 5

CRN 108-31-6

CMF C4 H2 O3



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